

TPD-8D12-016

GaAs PIN photodiode chip

FEATURES:

- Optimized for fiber optical application.
- Low dark current and low capacitance.

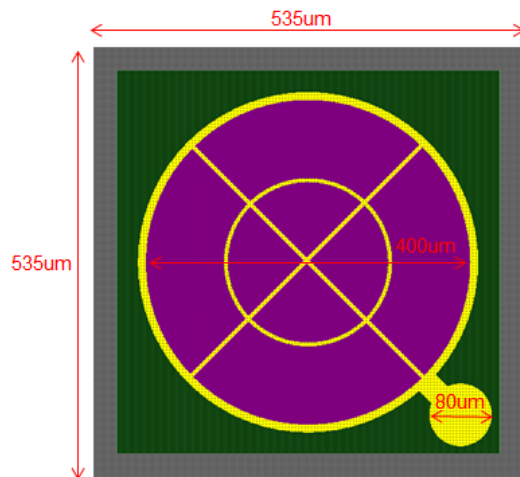
ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity	R	0.5	0.55		A/W	$V_R=1.5V$, $\lambda=850nm$ @ 25C
Dark Current	I_D		2	10	nA	$V_R=5V$ @ 25C
Breakdown Voltage	V_{BD}	50			V	$I_R=10\mu A$
Capacitance	C		4.5		pF	$V_R=1.5V$, $f=1$ MHz
Bandwidth	BW		700		MHz	$V_R=1.5V$

ABSOLUTE MAXIMUM RATINGS:

PARAMETERS	MIN	MAX	UNIT	CONDITIONS
Storage temperature	-40	100	°C	
Operating temperature	-40	85	°C	
Reverse current		2	mA	
Forward current		10	mA	
Reverse voltage		20	V	
Optical power		2	mW	

OUTLINE DIAGRAM:



- Chip size is typical 535x535 μm .
- Chip thickness is 200±12.5 μm
- Sensitive area is typical 400 μm in diameter.